# 2N7002K

RoHS

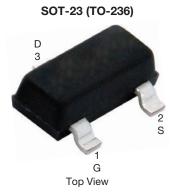
HALOGEN

FREE

**Vishay Siliconix** 

www.vishay.com

# N-Channel 60 V (D-S) MOSFET



## Marking code: 7K

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	60			
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = 10 V	2			
Q <sub>g</sub> typ. (nC)	0.4			
I <sub>D</sub> (A)	0.3			
Configuration	Single			

### **FEATURES**

- Low on-resistance: 2 Ω
- Low threshold: 2 V (typ.)
- Low input capacitance: 25 pF
- Fast switching speed: 25 ns
- · Low input and output leakage
- TrenchFET<sup>®</sup> power MOSFET
- 2000 V ESD protection
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### Note

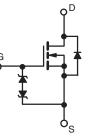
\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

#### **BENEFITS**

- Low offset voltage
- · Low voltage operation
- · Easily driven without buffer
- · High speed circuits
- · Low error voltage

#### **APPLICATIONS**

- Direct logic-level interface: TTL/CMOS
- Drivers: relays, solenoids, lamps, hammers, display, memories, transistors, etc.
- Battery operated systems
- Solid state relays



N-Channel MOSFET

ORDERING INFORMATION			
Package	SOT-23		
Lead (Pb)-free	2N7002K-T1-E3		
Lead (Pb)-free and halogen-free	2N7002K-T1-GE3		

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_A = 25 \text{ °C}$ , unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		V <sub>DS</sub>	60	V	
Gate-source voltage		V <sub>GS</sub>	± 20	v	
Continuous drain surrent (T $= 150 ^{\circ}\text{C})^{\text{b}}$	T <sub>A</sub> = 25 °C	1	0.3		
Continuous drain current (T <sub>J</sub> = 150 °C) <sup>b</sup>	T <sub>A</sub> = 100 °C	I <sub>D</sub>	0.19	А	
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	0.8		
Dower discipation b	T <sub>A</sub> = 25 °C	P	0.35	W	
Power dissipation <sup>b</sup>	T <sub>A</sub> = 100 °C	PD	0.14		
Maximum junction-to-ambient <sup>b</sup>		R <sub>thJA</sub>	350	°C/W	
Operating junction and storage temperature range		T <sub>J,</sub> T <sub>stg</sub>	-55 to +150	°C	

#### Notes

a. Pulse width limited by maximum junction temperature

b. Surface mounted on FR4 board

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP. <sup>a</sup>	MAX.	UNIT	
Static			•				
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, \text{ I}_D = 10 \mu\text{A}$	60	-	-	v	
Gate-threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	1	-	2.5	v	
Gate-body leakage		$V_{DS}=0~V,~V_{GS}=\pm~20~V$	-	-	± 10	μA	
		$V_{DS} = 0 V, V_{GS} = \pm 15 V$	′ 1		μΑ		
	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 10 V$	-	-	± 150	nA	
		$V_{DS}$ = 0 V, $V_{GS}$ = ± 10 V, T <sub>J</sub> = 85 °C	-	-	± 1000		
		$V_{DS} = 0 V$ , $V_{GS} = \pm 5 V$			± 100		
Zero gate voltage drain current	1	$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	1		1		
	I <sub>DSS</sub>	$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	500	μA	
On-state drain current <sup>b</sup>		$V_{GS} = 10 \text{ V}, V_{DS} = 7.5 \text{ V}$	800	-	-	— mA	
	I <sub>D(on)</sub>	$V_{GS} = 4.5 \text{ V}, V_{DS} = 10 \text{ V}$	500	-	-		
Drain-source on-resistance <sup>b</sup>	Passa	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 500 \text{ mA}$	-	-	2	Ω	
Drain-source on-resistance ~	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 200 \text{ mA}$	-	-	4		
Forward transconductance b	9 <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 200 \text{ mA}$	100	-	-	mS	
Diode forward voltage	V <sub>SD</sub>	$I_{S} = 200 \text{ mA}, V_{GS} = 0 \text{ V}$	-	-	1.3	V	
Dynamic <sup>a, b</sup>							
Total gate charge	Qg	$\begin{array}{l} V_{DS} = 10 \text{ V},  V_{GS} = 4.5 \text{ V} \\  I_{D} \cong 250 \text{ mA} \end{array}$	-	0.4	0.6	nC	
Input capacitance	C <sub>iss</sub>		-	30	-		
Output capacitance	C <sub>oss</sub>	$V_{DS} = 25 V, V_{GS} = 0 V$ f = 1 MHz	-	6	-	pF	
Reverse transfer capacitance	C <sub>rss</sub>		-	2.5	-	1	
Switching <sup>a, c</sup>			·				
Turn-on time	t <sub>d(on)</sub>	$V_{DD} = 30 \text{ V}, \text{ R}_{\text{I}} = 150 \Omega$	-	-	25		
Turn-off time	t <sub>d(off)</sub>	$I_D \cong 200 \text{ mA}, V_{GEN} = 10 \text{ V}, R_g = 10 \Omega$	-	-	35	ns	

Notes

a. For DESIGN AID ONLY, not subject to production testing

b. Pulse test: pulse width  $\leq$  300 µs duty cycle  $\leq$  2 %

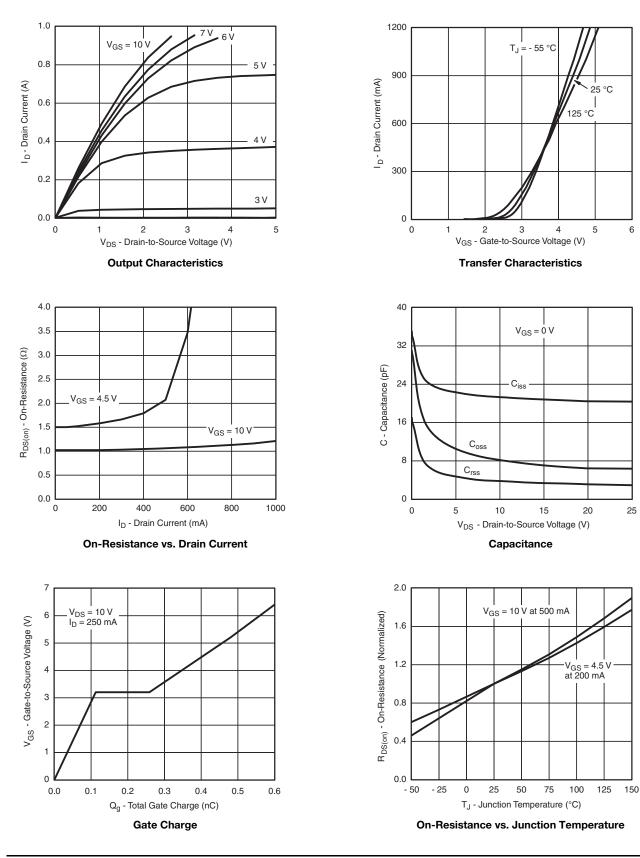
c. Switching time is essentially independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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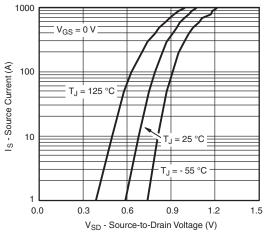
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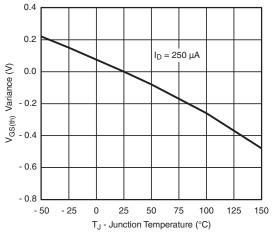
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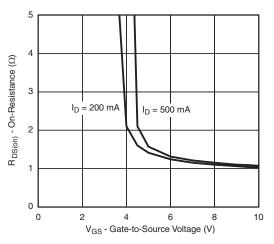
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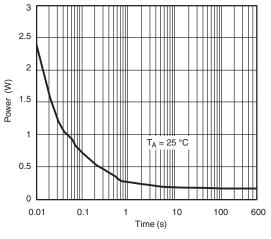
Source-Drain Diode Forward Voltage



Threshold Voltage Variance Over Temperature



**On-Resistance vs. Gate-Source Voltage** 



Single Pulse Power, Junction-to-Ambient

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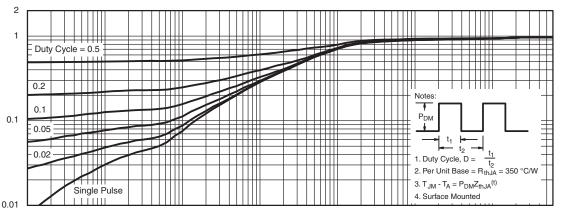


10<sup>-2</sup>

10<sup>-3</sup>

Normalized Effective Transient Thermal Impedance

10-4



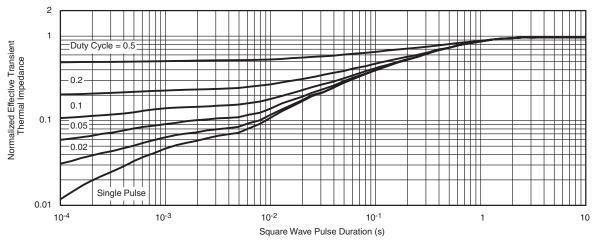


1

10

100

600



10-1

Normalized Thermal Transient Impedance, Junction-to-Foot

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# Package Information

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## SOT-23 (TO-236): 3-LEAD







Dim	MILLIMETERS		INCHES		
	Min	Max	Min	Мах	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	



# Application Note 826

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## **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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